



12.5Gbps 4-Channel, SAS3, 10GbE ReDriver with Linear Equalization

Features

- → 1-to-12.5Gbps serial link with linear equalizer
- → Supports SATA Gen1/Gen2/Gen3, SAS2/3, 10GbE, and XAUI protocol
- → Supports 4 differential channels
- → Handles up to 34dB channel loss (42" FR4 trace, 10 meters, or SAS3 cable)
- → Independent channel configuration of receiver equalization, output swing and flat gain
- → Rate and coding agnostic
- → Transparent to link training, OOB, Idle
- → 260mW per channel power dissipation with 700 mVpp output swing
- → Pin strap and I²C selectable device programming
- → 4-bit selectable address bit for I²C
- → Supply Voltage: 3.3V±0.3V
- → Industrial Temperature Range: -40°C to 85°C
- → Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- → Halogen and Antimony Free. "Green" Device (Note 3)
- → For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
 - https://www.diodes.com/quality/product-definitions/
- → Packaging (Pb-free & Green):
 - 42-contact TQFN (9mm x3.5mm)

Application

- → Rack Server
- → JBOD Storage

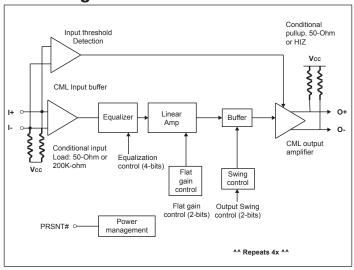
Description

The PI3EQX1204-C is a 4-differential-channel ReDriverTM. The device reduces Inter-symbol interference by providing programmable linear equalization in output swing and flat gain. This is achieved by using the pin strapping option or I^2C Control to optimize performance over a variety of physical mediums.

The PI3EQX1204-C supports four 100Ω differential CML data I/O's and extends the signals across other distant data pathways on the user's platform.

The integrated equalization circuitry provides signal integrity flexibility before the ReDriver, whereas the integrated linear amplifier/buffer circuitry provides signal integrity flexibility after the ReDriver.

Block Diagram



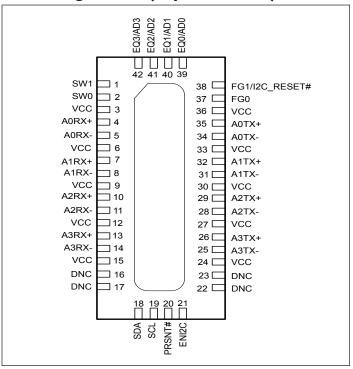
Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds





Pin Configuration (Top-Side View)



Pin Description

Pin#	Pin Name	Type	Description
Data Signals			
4	A0RX+	I	CML inputs for Channel A0, with internal 50 Ω pull-up and ~200K Ω
5	A0RX-	I	pull-up otherwise.
35	A0TX+	О	CML outputs for Channel A0, with internal 50 Ω pull-up and high
34	A0TX-	О	impedance otherwise.
7	A1RX+	I	CMI in the face Channel A1 with internal 500 well are and 200VO atherwise
8	A1RX-	I	CML inputs for Channel A1, with internal 50Ω pull-up and $\sim 200 \mathrm{K}\Omega$ otherwise.
32	A1TX+	О	CML outputs for Channel A1, with internal 50Ω pull-up and high
31	A1TX-	О	impedance otherwise.
10	A2RX+	I	CMI in the face Channel A2 with internal 500 million and 200VO athermical
11	A2RX-	I	CML inputs for Channel A2, with internal 50Ω pull-up and $\sim 200 \mathrm{K}\Omega$ otherwise.
29	A2TX+	О	CML outputs for Channel A2, with internal 50Ω pull-up and high
28	A2TX-	О	impedance otherwise.
13	A3RX+	I	
14	A3RX-	I	CML inputs for Channel A3, with internal 50Ω pull-up and $\sim 200 \mathrm{K}\Omega$ otherwise.
26	A3TX+	О	CML outputs for Channel A3, with internal 50Ω pull-up and high
25	A3TX-	О	impedance otherwise.





Pin Description Cont.

Pin #	Pin Name	Type	Description
Control Signals			•
19	SCL	I	I ² C SCL clock input.
18	SDA	I	I ² C SDA data input.
42, 41, 40, 39	AD[3:0]	I	I^2 C programmable address bits, with internal 100kΩ pull-up.
20	PRSNT#	I	This pin is active in both PIN mode(ENI2C=LOW) and I^2C mode (ENI2C=HIGH). Cable present detect input. This pin has internal $100K\Omega$ pull-up. When High, a cable is not present, and the device is put in lower power mode. When LOW, the device is enabled and in normal operation.
21	ENI2C	I	When LOW, each channel is programmed by the external pin voltage. When HIGH, each channel is programmed by the data stored in the I2C bus.
42, 41, 40, 39	EQ[3:0]	I	Inputs with internal $100k\Omega$ pull-up. This pins set the amount of Equalizer Boost in all channel when ENI2C is LOW.
1, 2	SW[1:0]	I	Inputs with internal $100k\Omega$ pull-up. This pin sets the output Voltage Level in all channel when ENI2C is LOW.
38, 37	FG[1:0]	I	Inputs with internal $100 \text{K}\Omega$ pull up resistor. Sets the output flat gain level on all channels when ENI2C is low.
38	I ² C_RESET#	I	Inputs with internal $100 \text{K}\Omega$ pull up resistor. Reset pin for $I^2\text{C}$. When set low will reset the registers to default state.
16, 17, 22, 23	DNC		Do Not Connect
Power Pins			
3, 6, 9, 12, 15, 24, 27, 30, 33, 36	VCC	PWR	3.3V Supply Voltage
EP	GND	PWR	Exposed pad. Supply Ground





Description of Operation

Power Enable function:

One pin control or I²C control, when PRSNT# is set to HIGH, the IC goes into power down mode, both input and output termination set to 200K and High impedance respectively. Individual Channel Enabling is done through the I²C register programming.

Equalization Setting:

EQ[3:0] are the selection pins for the equalization selection for each channel.

Table 1. Equalization Setting

	Equalizer setting									
EQ3	EQ2	EQ1	EQ0	@ 3GHz	@ 4GHz	@ 5GHz	@ 6GHz			
0	0	0	0	3.6	4.5	5.5	6.8			
0	0	0	1	4	5.1	6.2	7.6			
0	0	1	0	4.4	5.6	6.9	8.4			
0	0	1	1	4.7	6.1	7.5	9.1			
0	1	0	0	5.1	6.6	8.1	9.8			
0	1	0	1	5.5	7.1	8.7	10.4			
0	1	1	0	5.9	7.6	9.2	11			
0	1	1	1	6.2	8	9.7	11.5			
1	0	0	0	6.6	8.5	10.2	12			
1	0	0	1	6.9	8.9	10.7	12.5			
1	0	1	0	7.3	9.3	11.1	12.9			
1	0	1	1	7.6	9.7	11.5	13.3			
1	1	0	0	8	10.1	11.9	13.7			
1	1	0	1	8.2	10.5	12.3	14.1			
1	1	1	0	8.6	10.8	12.7	14.4			
1	1	1	1	8.9	11.1	13	14.7			





Flat Gain Setting:

FG[1:0] are the selection bits for the DC value.

Table 2. Flat Gain Setting

Flat Gain Setting					
FG1	FG0	dB			
0	0	-3.5			
0	1	-1.5			
1	0	0.5			
1	1	2.5			

Swing Setting:

Swing Setting: SW[1:0] are the selection bits for the output swing value.

Table 3. Swing Setting

SW1	SWO	mVp-p
0	0	700
0	1	800
1	0	900
1	1	1000





I²C Programming

Address assignment								
A6	A5	A4	A3	A2	A1	A0	R/W	
1	1	1	AD3	AD2	AD1	AD0	1=R, 0=W	

1	1	1	AD3	AD2	AD1	AD0		1=R, 0=W
BYTE 0	Reserved							
BYTE 1	Reserved							
BYTE 2	,							
Bit	Type	Power up condition			Control a	ffected	Com	ment
7	R/W	0			A3 Power	down		
6	R/W	0			A2 Power	down		
5	R/W	0			A1 Power	down		
4	R/W	0			A0 Power	down],	Power down
3	R/W	0] 1 = 1	ower down
2	R/W	0						
1	R/W	0						
0	R/W	0						
BYTE 3	,							
Bit	Type	Power up condition			Control	affected	Com	ment
7	R/W	0			EQ3			
6	R/W	0		Channel A0 configuration	EQ2		Faur	1:
5	R/W	0			EQ1		Equa	nzer
4	R/W	0	Chann		EQ0			
3	R/W	0	Citatiii		FG1		Flat gain	vain
2	R/W	0			FG0			gaiii
1	R/W	0			SW1		Swin	α
0	R/W	0					JWIII	g
BYTE 4	:							
Bit	Type	Power up condition			Control	affected	Com	ment
7	R/W	0			EQ3			
6	R/W	0			EQ2] _E	1:
5	R/W	0			EQ1		Equa	ıızer
4	R/W	0	Charre	al Al confermet:	EQ0			
3	R/W	0	Cnann	el A1 configuratio	r FG1		Elat	rain
2	R/W	0			FG0		Flat g	gaill
1	R/W	0			SW1		Swin	σ
0	R/W	0			SW0		SWIII	წ





I²C Programming cont.

Bit	Type	Power up condition		Control affected	Comment	
7	R/W	0		EQ3		
6	R/W	0		EQ2]	
5	R/W	0		EQ1	Equalizer	
4	R/W	0		EQ0		
3	R/W	0	Channel A2 configuration	FG1	T1	
2	R/W	0		FG0	Flat gain	
1	R/W	0		SW1		
0	R/W	0		SW0	Swing	
вүте е	5					
Bit	Type	Power up condition		Control affected	Comment	
Bit 7	Type R/W	Power up condition		Control affected EQ3	Comment	
7	R/W	0		EQ3	Comment Equalizer	
7 6 5	R/W R/W	0 0		EQ3 EQ2		
7	R/W R/W R/W	0 0 0	Channel A3 configuration	EQ3 EQ2 EQ1	- Equalizer	
7 6 5 4	R/W R/W R/W R/W	0 0 0 0	Channel A3 configuration	EQ3 EQ2 EQ1 EQ0		
7 6 5 4 3	R/W R/W R/W R/W	0 0 0 0	Channel A3 configuration	EQ3 EQ2 EQ1 EQ0 FG1	- Equalizer	





Transferring Data

Every byte put on the SDA line must be 8-bits long. Each byte has to be followed by an acknowledge bit. Data is transferred with the most significant bit (MSB) first (see the I^2C Data Transfer diagram).

Acknowledge

Data transfer with acknowledge is required from the master. When the master releases the SDA line (HIGH) during the acknowledge clock pulse, the PI3EQX1204-C will pull down the SDA line during the acknowledge clock pulse so that it remains stable LOW during the HIGH period of this clock pulse as indicated in the I²C Data Transfer diagram. The PI3EQX1204-C will generate an acknowledge after each byte has been received.

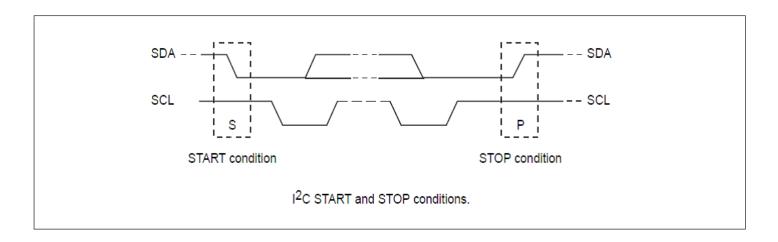
Data Transfer

A data transfer cycle begins with the master issuing a start bit. After recognizing a start bit, the PI3EQX1204-C will watch the next byte of information for a match with its address setting. When a match is found it will respond with a read or write of data on the following clocks. Each byte must be followed by an acknowledge bit, except for the last byte of a read cycle which ends with a stop bit. For a write cycle, the first data byte following the address byte is an index byte that is used by the PI3EQX1204-C. Data is transferred with the most significant bit (MSB) first.

I2C Data Transfer

Start & Stop Conditions

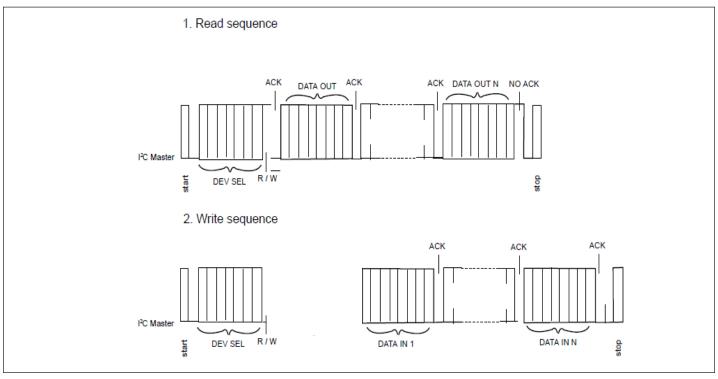
A HIGH to LOW transition on the SDA line while SCL is HIGH indicates a START condition. A LOW to HIGH transition on the SDA line while SCL is HIGH defines a STOP condition, as shown in the figure below







I²C Data Transfer







Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature
Supply Voltage to Ground Potential $-0.5V$ to $+4.6V$
DC SIG Voltage
Output Current25mA to +25mA
Power Dissipation Continuous
Junction Temperature Tj
ESD, HBM2kV to +2kV

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Electrical Characteristics:

LVCMOS I/O DC Specifications ($V_{CC} = 3.3 \pm 0.3 V$, $T_A = -40 \text{ to } 85 ^{\circ}\text{C}$)

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
V_{IH}	DC input logic high		$V_{CC}/2 + 0.7$		$V_{C}C + 0.3$	V
V_{IL}	DC input logic low		-0.3		V _{CC} /2 - 0.7	V
V _{OH}	At IOH = -200μA		$V_{CC} + 0.2$			V
V _{OL}	At IOL = -200μ A				0.2	V
V _{hys}	Hysteresis of Schmitt trigger input		0.8			V

SDA and **SCL I/O** for **I2C-bus** ($V_{CC} = 3.3 \pm 0.3 \text{V}$, $T_A = -40 \text{ to } 85^{\circ}\text{C}$)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V_{IH}	DC input logic high		$V_{CC}/2 + 0.7$		$V_{CC} + 0.3$	V
V_{IL}	DC input logic low		-0.3		V _{CC} /2 - 0.7	V
V _{OL}	DC output logic low	$I_{OL} = 3mA$			0.4	V
V _{hys}	Hysteresis of Schmitt trigger input		0.8			V
t _{of}	Output fall time from VIHmin to VILmax with bus cap. 10-400pF				250	ns
f _{SCLK}	SCLK clock frequency				100	kHz

High Speed I/O AC/DC Specifications ($V_{CC} = 3.3 \pm 0.3 \text{V}$, $T_{A} = -40 \text{ to } 85^{\circ}\text{C}$)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
C_{RX}	RX AC coupling capacitance			220		nF
S ₁₁	Imput noturn loss	10MHz to 6GHz differential		11.0		dB
	Input return loss	1GHz to 6GHz common mode		5.0		ав
C	10MHz to 6GHz differential			11.5		dB
S ₂₂	Output return loss	1GHz to 6GHz common mode		4.8		ub
D	DC single-ended input impedance			50		0
R _{IN}	DC Differential Input Impedance			100		Ω





High Speed I/O AC/DC Specifications Cont.

Symbol	ol Parameter Conditions		Min.	Тур.	Max.	Units	
D	DC single-ended output impedance			50			
R _{OUT}	DC Differential output Impedance			100		Ω	
Z _{RX-HIZ}	DC input CM input impedance during reset or power down			200		kΩ	
V _{RX-DIFF-PP}	Differential Input Peak-to-peak Voltage	Operational			1.2	Vppd	
	Input source common-mode noise	DC – 200MHz			150	mVpp	
T _{TX-IDLE-SET-TO-} IDLE	Max time to electrical idle after sending an EIOS			4	8	ns	
T _{TX-IDLE-TO-DIFF-} DATA	Max time to valid diff signal after leaving electrical idle			4	8	ns	
Vcc	Power supply voltage		3	3.3	3.6	V	
P _{max}	Max Supply power	PRSNT#=0			1.3	W	
I _{max}	Max Supply current				360	mA	
P _{idle}	Supply power	PRSNT#=1			14.4	mW	
t _{pd}	Latency	From input to output		0.5		ns	
Gp	Peaking gain (Compensation at 6GHz, relative to 100MHz, 100mVp-p sine wave input)	EQ<3:0> = 1111		15.4		dB	
		EQ<3:0> = 1000		12.5			
		EQ<3:0> = 0000		7.1			
		Variation around typical	-3		+3	dB	
G_{F}	Flat gain (100MHz, EQ<3:0> = 1000, SW<1:0> = 10)	FG<1:0> = 11		2		dB	
		FG<1:0> = 10		0			
		FG<1:0> = 01		-2			
		FG<1:0> = 00		-4			
		Variation around typical	-3		+3	dB	
V _{1dB_100M}	-1dB compression point of output swing (at 100MHz)	SW<1:0> = 11		1370		mVppd	
		SW<1:0> = 10		1280			
		SW<1:0> = 01		1040			
		SW<1:0> = 00		920			
V _{1dB_6} G	-1dB compression point of output swing (at 6GHz)	SW<1:0> = 11		1000		mVppd	
		SW<1:0> = 10		940			
		SW<1:0> = 01		700			
		SW<1:0> = 00		600			
V_{Coup}	Channel isolation	100MHz to 6GHz ⁽¹⁾ , Figure 1 25				dB	





High Speed I/O AC/DC Specifications Cont.

Symbol	Parameter	Conditions M		Тур.	Max.	Units
Vnoise_input	Input-referred noise	100MHz to 6GHz, FG<1:0> = 11, EQ<3:0> = 0000, Figure 2	0.5			37
		100MHz to 6GHz, FG<1:0> = 11, EQ<3:0> = 1010, Figure 2		0.4		mV _{RMS}
Vnoise_output		100MHz to 6GHz, FG<1:0> = 11, EQ<3:0> = 0000, Figure 2		0.7		***
	Output-referred noise ⁽²⁾	100MHz to 6GHz, FG<1:0> = 11, EQ<3:0> = 1010, Figure 2		0.8	1.6	mV _{RMS}

Note: (1) Measured using a vector-network analyzer (VNA) with -15dBm power level applied to the adjacent input. The VNA detects the signal at the output of the victim channel. All other inputs and outputs are terminated with 50Ω .

(2) Guaranteed by design and characterization.

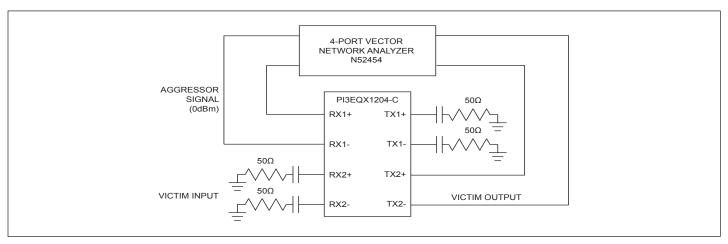


Figure 1. Channel-Isolation Test Configuration

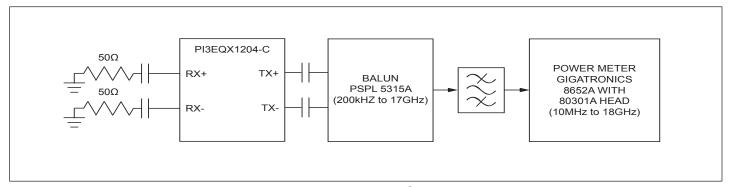


Figure 2. Noise Test Configuration

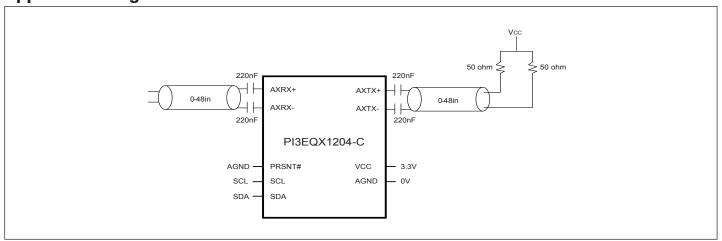




ESD Specification

- 2000V HBM
- 500V CDM

Application Diagram







AC/DC Specifications - SCL/SDA for I²C BUS

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
V _{IH}	DC input logic high		V _{CC} /2 + 0.7		V _{CC} + 0.3	V
$V_{\rm IL}$	DC input logic low		-0.3		V _{CC} /2 - 0.7	V
V _{OL}	DC output logic low	$I_{OL} = 3mA$			0.4	V
Ipullup	Current Through Pull-Up Resistor or Current Source	High Power specification	3.0		3.6	mA
VDD	Nominal Bus Voltage		3.0		3.6	V
Ileak-bus	Input leakage per bus segment		-200		200	uA
Ileak-pin	Input leakage per device pin			-15		uA
CI	Capacitance for SDA/SCL				10	pF
Freq	Bus Operation Frequency				100k	Hz
TBUF	"Bus Free Time Between Stop and Start condition"		1.3			us
THD:STA	Hold time after (Repeated) Start condition. After this period, the first clock is generated.	At Ipull-up, Max	0.6			us
TSU:STA	Repeated start condition setup time		0.6			us
TSU:STO	Stop condition setup time		0.6			us
THD:DAT	Data hold time		0			ns
TSU:DAT	Data setup time		100			ns
Tlow	Clock low period		1.3			us
Thigh	Clock high period		0.6		50	us
tF	Clock/Data fall time				300	ns
tR	Clock/Data rise time				300	ns
tpor	"Time in which a device must be operation after power-on reset"				500	ms

Note: (1) Recommended value.

- (2) Recommended maximum capacitance load per bus segment is $400 \mathrm{pF}.$
- (3) Compliant to I²C physical layer specification.
- (4) Ensured by Design. Parameter not tested in production.

Part Marking



Z: Die Rev YY: Year

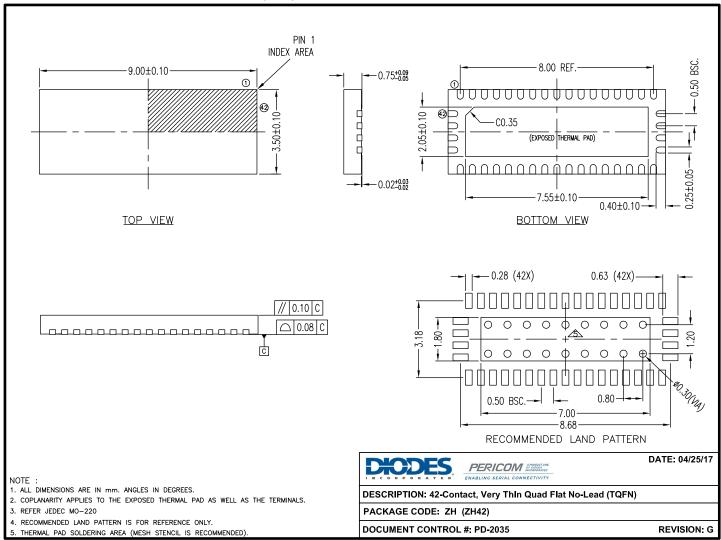
WW: Workweek

1st X: Assembly Code 2nd X: Fab Code





Package Mechanical: 42-TQFN (ZH)



17-0266

For latest package info.

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Ordering Information

Ordering Number	Package Code	Package Description
PI3EQX1204-CZHEX	ZH	42-Contact, Very Thin Quad Flat No-Lead (TQFN)

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- $2. \ \ See \ https://www.diodes.com/quality/lead-free/\ for\ more\ information\ about\ Diodes\ Incorporated's\ definitions\ of\ Halogen-\ and\ Antimony-free,\ "Green"\ and\ Lead-free.$
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel





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